

VHF POWER MOSFET

N-Channel Enhancement Mode

DESCRIPTION:

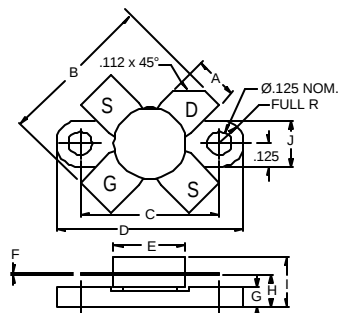
The **VFT15-28** is Designed for General Purpose Class B Power Amplifier Applications up to 175 MHz.

FEATURES:

- $P_G = 14$ dB Typ. at 15 W /175MHz
- 10:1 Load VSWR Capability
- *Omnigold™* Metalization System

MAXIMUM RATINGS

I_D	2.5 A
$V_{(BR)DSS}$	65 V
V_{DGR}	65 V
V_{GS}	± 40 V
P_{DISS}	55 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
q_{JC}	3.2°C/W

PACKAGE STYLE .380 4L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

ORDER CODE: ASI10702
CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
$V_{(BR)DSS}$	$V_{GS} = 0$ V	$I_{DS} = 5.0$ mA	60	---	---	V
I_{DSS}	$V_{DS} = 28$ V	$V_{GS} = 0$ V	---	---	2.0	mA
I_{GSS}	$V_{DS} = 0$ V	$V_{GS} = 40$ V	---	---	1.0	mA
V_{GS}	$V_{DS} = 10$ V	$I_D = 25$ mA	1.0	---	6.0	V
G_{FS}	$V_{DS} = 10$ V	$I_D = 250$ mA	250	---	---	mS
C_{iss} C_{oss} C_{rss}	$V_{GS} = 28$ V	$V_{DS} = 0$ V		22 17 3.0		pF
P_G h_D	$V_{DD} = 28$ V F = 175 MHz	$I_{DQ} = 25$ mA $P_{OUT} = 15$ W	13 50	14 60		dB %



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